ENHANCED FREE LAYER FOR A SPIN VALVE SENSOR

ABSTRACT OF THE DISCLOSURE

A spin valve sensor is provided with a negative ferromagnetic coupling field -H_{FC} for properly biasing a free layer and a spin filter layer is employed between the free layer and a capping layer for increasing the magnetoresistive coefficient dr/R of the spin valve sensor. A top portion of the free layer is oxidized for improving the negative ferromagnetic coupling field -H_{FC} when the spin filter layer is employed for increasing the magnetoresistive coefficient dr/R.

10